PD - 91810

International
IOR Rectifier

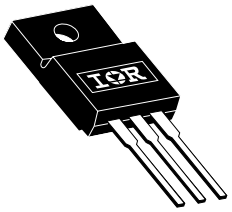
SMPS MOSFET # IRFIB7N50A

HEXFET® Power MOSFET

V_{DSS}	Rds(on) max	I_D
500V	**0.52Ω**	**6.6A**

Applications
- Switch Mode Power Supply (SMPS)
- Uninterruptable Power Supply
- High speed power switching
- High Voltage Isolation = 2.5KVRMS⑦

Benefits
- Low Gate Charge Qg results in Simple Drive Requirement
- Improved Gate, Avalanche and dynamic dv/dt Ruggedness
- Fully Characterized Capacitance and Avalanche Voltage and Current
- Effective Coss specified (See AN 1001)



G D S

TO-220 FULLPAK

Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	6.6	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	4.2	
I_{DM}	Pulsed Drain Current ①⑥	44	
P_D @T_C = 25°C	Power Dissipation	60	W
	Linear Derating Factor	0.48	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③⑥	6.9	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torqe, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Applicable Off Line SMPS Topologies:

- Two Transistor Forward
- Half & Full Bridge Convertors
- Power Factor Correction Boost

Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.61	—	V/°C	Reference to 25°C, I_D = 1mA⑥
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.52	Ω	V_{GS} = 10V, I_D = 4.0A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	µA	V_{DS} = 500V, V_{GS} = 0V
		—	—	250		V_{DS} = 400V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -30V

Dynamic @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	6.1	—	—	S	V_{DS} = 50V, I_D = 6.6A⑥
Q_g	Total Gate Charge	—	—	52	nC	I_D = 11A
Q_{gs}	Gate-to-Source Charge	—	—	13		V_{DS} = 400V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	18		V_{GS} = 10V, See Fig. 6 and 13 ④⑥
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	V_{DD} = 250V
t_r	Rise Time	—	35	—		I_D = 11A
$t_{d(off)}$	Turn-Off Delay Time	—	32	—		R_G = 9.1Ω
t_f	Fall Time	—	28	—		R_D = 22Ω,See Fig. 10 ④⑥
C_{iss}	Input Capacitance	—	1423	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	208	—		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	—	8.1	—		f = 1.0MHz, See Fig. 5⑥
C_{oss}	Output Capacitance⑥	—	2000	—		V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance⑥	—	55	—		V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz
C_{oss} eff.	Effective Output Capacitance	—	97	—		V_{GS} = 0V, V_{DS} = 0V to 400V ⑤⑥

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②⑥	—	275	mJ
I_{AR}	Avalanche Current①⑥	—	11	A
E_{AR}	Repetitive Avalanche Energy①	—	6.0	mJ

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	2.1	°C/W
$R_{\theta JA}$	Junction-to-Ambient	—	65	

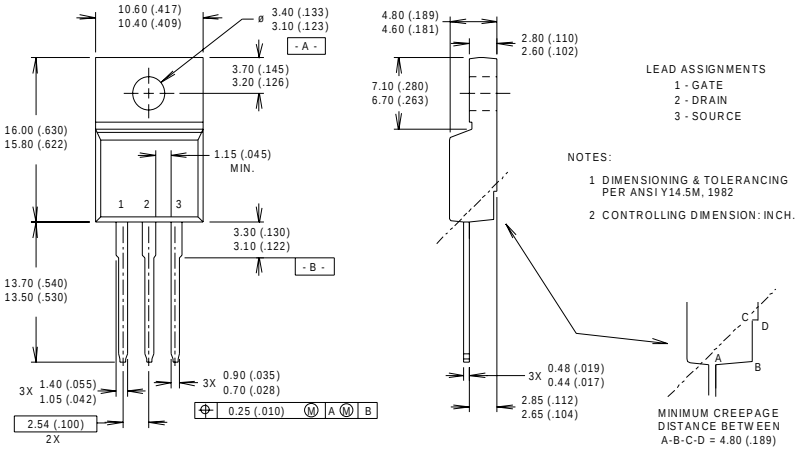
Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	6.6	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①⑥	—	—	44		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	T_J = 25°C, I_S = 11A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	510	770	ns	T_J = 25°C, I_F = 11A
Q_{rr}	Reverse RecoveryCharge	—	3.4	5.1	µC	di/dt = 100A/µs ④⑥
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Package Outline

TO-220 Fullpak Outline

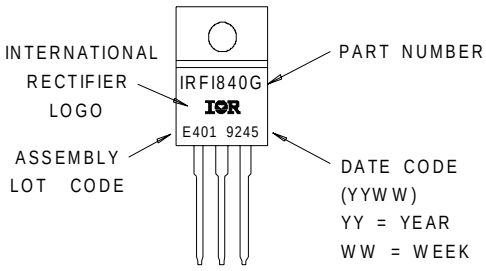
Dimensions are shown in millimeters (inches)



Part Marking Information

TO-220 Fullpak

EXAMPLE : THIS IS AN IRFI840G
WITH ASSEMBLY
LOT CODE E401



Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 4.5mH R_G = 25Ω, I_{AS} = 11A. (See Figure 12)

③ $I_{SD} \leq$ 11A, di/dt ≤140A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 150°C

④ Pulse width ≤ 300µs; duty cycle ≤ 2%.

⑤ C_{oss} eff. is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}

⑥ Uses IRFB11N50A data and test conditions

⑦ t=60s,f=60Hz